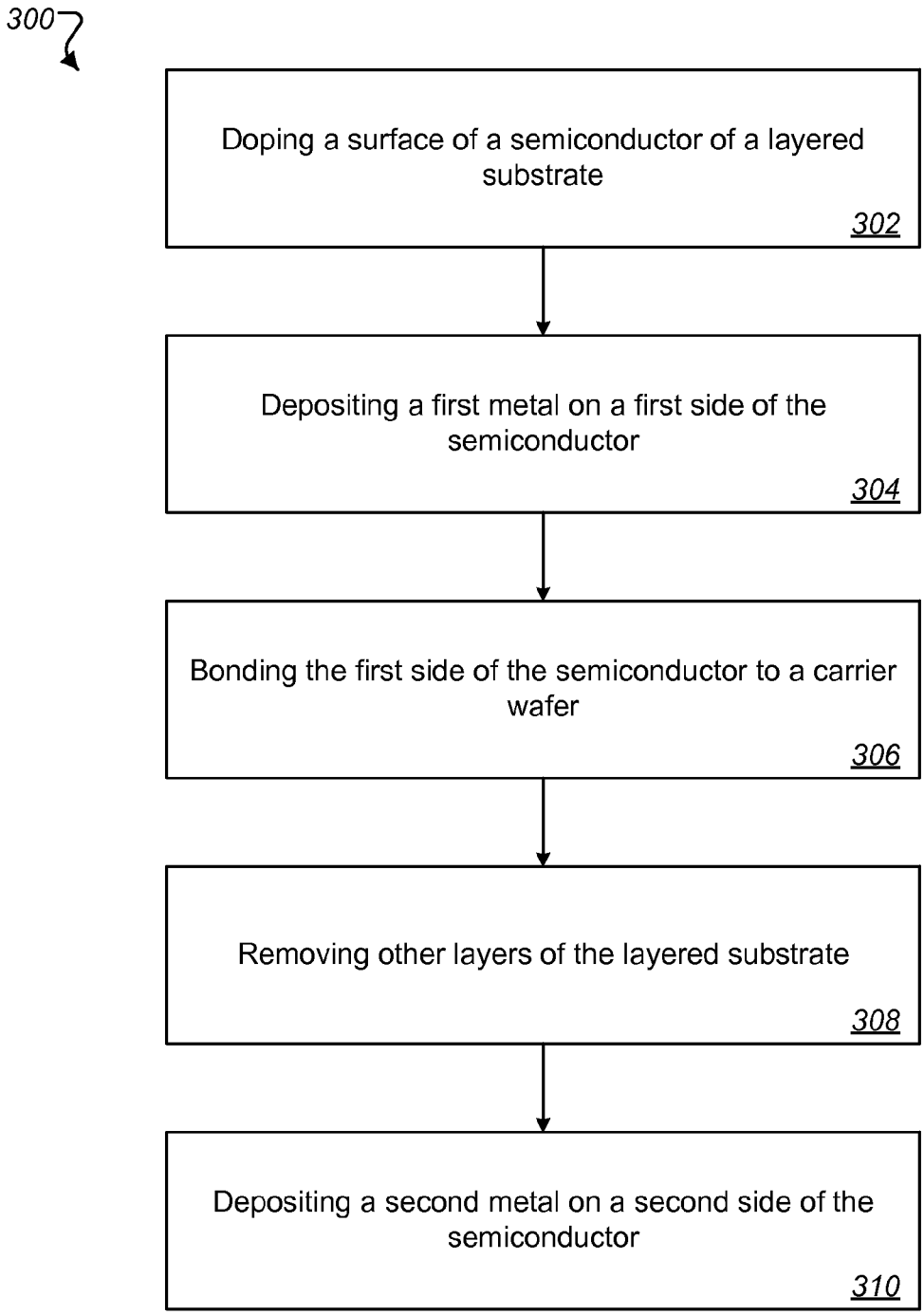
300
Doping a surface of a semiconductor of a layered substrate
302
Depositing a first metal on a first side of the semiconductor
304
Bonding the first side of the semiconductor to a carrier wafer
306
Removing other layers of the layered substrate
308
Depositing a second metal on a second side of the semiconductor
310

FIG. 3